# **Digital Transistors (BRT)** R1 = 100 k $\Omega$ , R2 = $\infty$ k $\Omega$

### **PNP Transistors with Monolithic Bias Resistor Network**

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a baseemitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

### **Features**

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### **MAXIMUM RATINGS** $(T_A = 25^{\circ}C)$

Rating	Symbol	Max	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	Vdc
Collector-Emitter Voltage	$V_{CEO}$	50	Vdc
Collector Current – Continuous	I <sub>C</sub>	100	mAdc
Input Forward Voltage	V <sub>IN(fwd)</sub>	40	Vdc
Input Reverse Voltage	V <sub>IN(rev)</sub>	5	Vdc

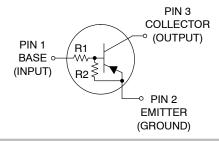
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



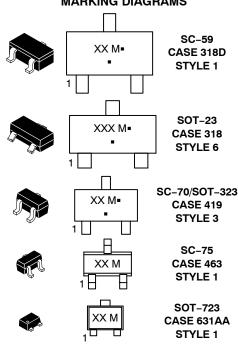
### ON Semiconductor®

www.onsemi.com

### PIN CONNECTIONS



### **MARKING DIAGRAMS**



XXX = Specific Device Code M = Date Code\*

IX MIL 1

= Pb-Free Package (Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

### ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

SOT-1123

CASE 524AA STYLE 1

**Table 1. ORDERING INFORMATION** 

Device	Part Marking	Package	Shipping <sup>†</sup>
MUN2141T1G	6Y	SC-59 (Pb-Free)	3000 / Tape & Reel
MMUN2141LT1G	ACH	SOT-23 (Pb-Free)	3000 / Tape & Reel
MUN5141T1G	6T	SC-70/SOT-323 (Pb-Free)	3000 / Tape & Reel
DTA115TET1G	6U	SC-75 (Pb-Free)	3000 / Tape & Reel
DTA115TM3T5G	7G	SOT-723 (Pb-Free)	8000 / Tape & Reel
NSBA115TF3T5G	Q (90°)*	SOT-1123 (Pb-Free)	8000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\* (</sup>xx°) = Degree rotation in the clockwise direction.

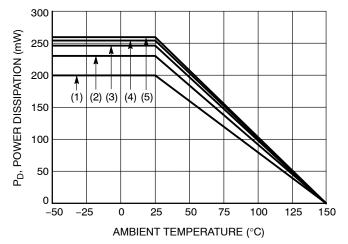


Figure 1. Derating Curve

- (1) SC-75 and SC-70/SOT323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-1123; 100 mm<sup>2</sup>, 1 oz. copper trace
- (5) SOT-723; Minimum Pad

**Table 2. THERMAL CHARACTERISTICS** 

Characteristic		Symbol	Max	Unit
THERMAL CHARACTERISTICS (SC-59) (MUN2141)			•	
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P <sub>D</sub>	230 338 1.8 2.7	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ heta JA}$	540 370	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ hetaJL}$	264 287	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERISTICS (SOT-23) (MMUN2141L)				
Total Device Dissipation $T_{A} = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P <sub>D</sub>	246 400 2.0 3.2	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	508 311	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ hetaJL}$	174 208	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERISTICS (SC-70/SOT-323) (MUN5141)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P <sub>D</sub>	202 310 1.6 2.5	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	618 403	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ hetaJL}$	280 332	°C/W
Junction and Storage Temperature Range		$T_J$ , $T_{stg}$	-55 to +150	°C
THERMAL CHARACTERISTICS (SC-75) (DTA115TE)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P <sub>D</sub>	200 300 1.6 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	600 400	°C/W
Junction and Storage Temperature Range		$T_J$ , $T_{stg}$	-55 to +150	°C
THERMAL CHARACTERISTICS (SOT-723) (DTA115TM3)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P <sub>D</sub>	260 600 2.0 4.8	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	480 205	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

- 1. FR-4 @ Minimum Pad.

- 2. FR-4 @ 1.0 x 1.0 lnch Pad.
  3. FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
  4. FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

**Table 2. THERMAL CHARACTERISTICS** 

Characteristic		Symbol	Max	Unit
THERMAL CHARACTERISTICS (SOT-1123) (NSBA115TF3)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 3) (Note 4) (Note 3) (Note 4)	P <sub>D</sub>	254 297 2.0 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 3) (Note 4)	$R_{ hetaJA}$	493 421	°C/W
Thermal Resistance, Junction to Lead	(Note 3)	$R_{ hetaJL}$	193	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

<sup>1.</sup> FR-4 @ Minimum Pad.

Table 3. ELECTRICAL CHARACTERISTICS ( $T_A = 25$ °C, unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector-Base Cutoff Current (V <sub>CB</sub> = 50 V, I <sub>E</sub> = 0)	I <sub>CBO</sub>	_	_	100	nAdc
Collector-Emitter Cutoff Current (V <sub>CE</sub> = 50 V, I <sub>B</sub> = 0)	I <sub>CEO</sub>	-	-	500	nAdc
Emitter–Base Cutoff Current $(V_{EB} = 6.0 \text{ V, } I_C = 0)$	I <sub>EBO</sub>	-	-	0.1	mAdc
Collector-Base Breakdown Voltage ( $I_C = 10 \mu A, I_E = 0$ )	V <sub>(BR)</sub> CBO	50	_	-	Vdc
Collector-Emitter Breakdown Voltage (Note 5) (I <sub>C</sub> = 2.0 mA, I <sub>B</sub> = 0)	V <sub>(BR)</sub> CEO	50	-	-	Vdc
ON CHARACTERISTICS	·				
DC Current Gain (Note 5) (I <sub>C</sub> = 5.0 mA, V <sub>CE</sub> = 10 V)	h <sub>FE</sub>	160	350	-	
Collector–Emitter Saturation Voltage (Note 5) $(I_C = 10 \text{ mA}, I_B = 0.3 \text{ mA})$	V <sub>CE(sat)</sub>	_	-	0.25	Vdc
Input Voltage (off) $(V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A})$	$V_{i(off)}$	_	0.6	0.5	Vdc
Input Voltage (on) $(V_{CE} = 0.3 \text{ V, } I_{C} = 1.0 \text{ mA})$	V <sub>i(on)</sub>	1.5	1.0	-	Vdc
Output Voltage (on) $(V_{CC} = 5.0 \text{ V}, V_B = 2.5 \text{ V}, R_L = 1.0 \text{ k}\Omega)$	V <sub>OL</sub>	_	_	0.2	Vdc
Output Voltage (off) $(V_{CC} = 5.0 \text{ V}, V_B = 0.5 \text{ V}, R_L = 1.0 \text{ k}\Omega)$	V <sub>OH</sub>	4.9	-	-	Vdc
Input Resistor	R1	70	100	130	kΩ
Resistor Ratio	$R_1/R_2$	-	-	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.

FR-4 @ 1.0 x 1.0 Inch Pad.
 FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
 FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

# TYPICAL CHARACTERISTICS MUN2141, MMUN2141, MUN5141, DTA115TE, DTA115TM3, NSBA115TF3

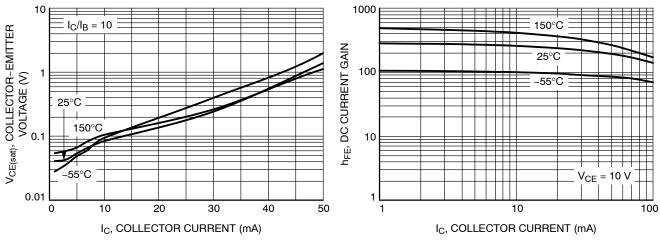


Figure 2. V<sub>CE(sat)</sub> vs. I<sub>C</sub>

Figure 3. DC Current Gain

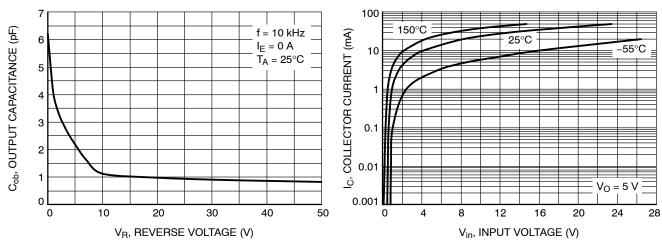


Figure 4. Output Capacitance

Figure 5. Output Current vs. Input Voltage

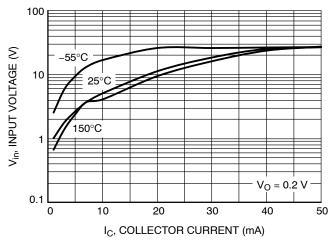


Figure 6. Input Voltage vs. Output Current

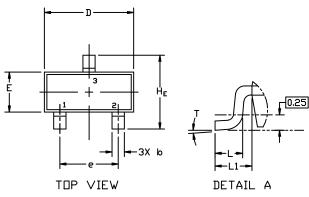




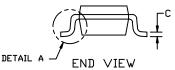
SOT-23 (TO-236) **CASE 318 ISSUE AT** 

**DATE 01 MAR 2023** 









### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- CONTROLLING DIMENSION: MILLIMETERS
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIM	MILLIMETERS			INCHES		
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.	
A	0.89	1.00	1.11	0.035	0.039	0.044	
A1	0.01	0.06	0.10	0.000	0.002	0.004	
b	0.37	0.44	0.50	0.015	0.017	0.020	
U	0.08	0.14	0.20	0.003	0.006	0.008	
D	2.80	2.90	3.04	0.110	0.114	0.120	
E	1.20	1.30	1.40	0.047	0.051	0.055	
e	1.78	1.90	2.04	0.070	0.075	0.080	
L	0.30	0.43	0.55	0.012	0.017	0.022	
L1	0.35	0.54	0.69	0.014	0.021	0.027	
HE	2.10	2.40	2.64	0.083	0.094	0.104	
T	0*		10*	0*		10°	



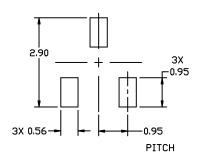


XXX = Specific Device Code

= Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

### **STYLES ON PAGE 2**

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DESCRIPTION:	SOT-23 (TO-236)		PAGE 1 OF 2

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# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



### **SOT-23 (TO-236)** CASE 318 ISSUE AT

**DATE 01 MAR 2023** 

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	ı	
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE		PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE		2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE		3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	I PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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DESCRIPTION:	SOT-23 (TO-236)		PAGE 2 OF 2

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SCALE 2:1

SC-59 CASE 318D-04 ISSUE H

**DATE 28 JUN 2012** 

### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	MOM	MAX
Α	1.00	1.15	1.30	0.039	0.045	0.051
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.35	0.43	0.50	0.014	0.017	0.020
С	0.09	0.14	0.18	0.003	0.005	0.007
D	2.70	2.90	3.10	0.106	0.114	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
е	1.70	1.90	2.10	0.067	0.075	0.083
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.80	3.00	0.099	0.110	0.118

### **GENERIC MARKING DIAGRAM**



XXX = Specific Device Code

Μ = Date Code

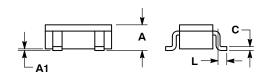
= Pb-Free Package\* (\*Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

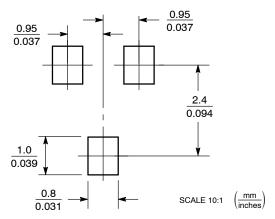
STYLE 1:		STYLE 2:		STYLE 3:	
PIN 1.	BASE	PIN 1.	ANODE	PIN 1.	ANODE
2.	EMITTER	2.	N.C.	2.	ANODE
3.	COLLECTOR	3.	CATHODE	3.	CATHODE

STYLE 4:	STYLE 5:	STYLE 6:
PIN 1. CATHODE	PIN 1. CATHODE	PIN 1. ANODE
2. N.C.	2. CATHODE	2. CATHODE
3. ANODE	3. ANODE	<ol><li>ANODE/CATHODE</li></ol>

# $H_{E}$



### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	SC-59	•	PAGE 1 OF 1

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SC-70 (SOT-323) **CASE 419** ISSUE R

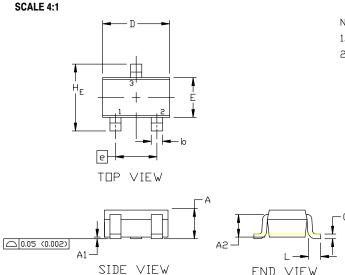
END VIEW

**DATE 11 OCT 2022** 

### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	MILLIMETERS				INCHES	
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.70 REF			0.028 BS	C
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BS	C	
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095



### **GENERIC MARKING DIAGRAM**

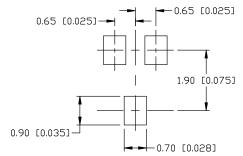


= Specific Device Code XX

Μ = Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.



For additional information on our Pb-Free strategy and soldering details, please download the ID Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6: PIN 1. EMITTER	STYLE 7: PIN 1. BASE	STYLE 8: PIN 1. GATE	STYLE 9: PIN 1. ANODE	STYLE 10: PIN 1. CATHODE	STYLE 11: PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	2. CATHODE
<ol><li>COLLECTOR</li></ol>	<ol><li>COLLECTOR</li></ol>	3. DRAIN	<ol><li>CATHODE-ANODE</li></ol>	3. ANODE-CATHODE	<ol><li>CATHODE</li></ol>

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DESCRIPTION:	SC-70 (SOT-323)		PAGE 1 OF 1

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## **MECHANICAL CASE OUTLINE**

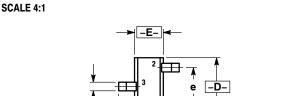
b 3 PL ⊕ 0.20 (0.008) M D

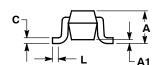




SC-75/SOT-416 CASE 463-01 ISSUE G

**DATE 07 AUG 2015** 





STYLE 1: PIN 1. BASE 2. EMITTER

3. COLLECTOR

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN

STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE

STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE

0.20 (0.008) E

### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS				INCHES	;
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.70	0.80	0.90	0.027	0.031	0.035
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.15	0.20	0.30	0.006	0.008	0.012
С	0.10	0.15	0.25	0.004	0.006	0.010
D	1.55	1.60	1.65	0.061	0.063	0.065
Е	0.70	0.80	0.90	0.027	0.031	0.035
е	1	.00 BSC	)		0.04 BSC	)
L	0.10	0.15	0.20	0.004	0.006	0.008
HE	1.50	1.60	1.70	0.060	0.063	0.067

### **GENERIC MARKING DIAGRAM\***



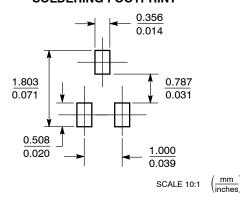
XX= Specific Device Code

Μ = Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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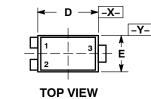
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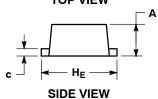


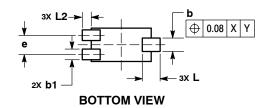
SOT-1123 CASE 524AA ISSUE C

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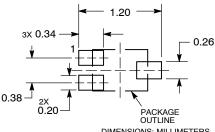
### SCALE 8:1







### **SOLDERING FOOTPRINT\***



**DIMENSIONS: MILLIMETERS** \*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and

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### NOTES:

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

  2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE
- MINIMUM THICKNESS OF BASE MATERIAL.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD
  FLASH, PROTRUSIONS, OR GATE BURRS.

	<b>MILLIMETERS</b>				
DIM	MIN	MAX			
Α	0.34	0.40			
b	0.15	0.28			
b1	0.10	0.20			
С	0.07	0.17			
D	0.75	0.85			
E	0.55	0.65			
е	0.35	0.40			
HE	0.95	1.05			
L	0.185	REF			
L2	0.05	0.15			

### **GENERIC MARKING DIAGRAM\***



= Specific Device Code

Μ = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
2. EMITTER	2. N/C	2. ANODE	2. CATHODE	2. SOURCE
<ol><li>COLLECTOR</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>ANODE</li></ol>	3. DRAIN

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- C

SIDE VIEW

**DATE 10 AUG 2009** 

### NOTES:

- NOTES.

  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

  2. CONTROLLING DIMENSION: MILLIMETERS.

  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD
- FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

	MILLIMETERS				
DIM	MIN	NOM	MAX		
Α	0.45	0.50	0.55		
b	0.15	0.21	0.27		
b1	0.25	0.31	0.37		
С	0.07	0.12	0.17		
D	1.15	1.20	1.25		
E	0.75	0.80	0.85		
е		0.40 BS0			
ΗE	1.15	1.20	1.25		
L	0.29 REF				
12	0.15	0.20	0.25		

# **L2** 0.15 0.20 0.25

### **GENERIC MARKING DIAGRAM\***

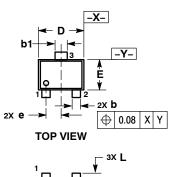


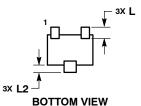
= Specific Device Code XX

Μ = Date Code



\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present.

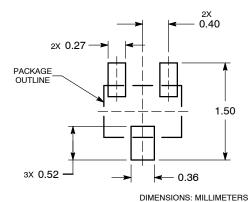




STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN

### **RECOMMENDED SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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